Electronic Supplementary Information (ESI)

Low-temperature ALD/MLD growth of alucone and zincone thin films from non-pyrophoric precursors

Anish Philip[a¥], Lukas Mai[b¥], Ramin Ghiyasi[a], Anjana Devi[b*], and Maarit Karppinen[a*]

[a] *Department of Chemistry and Materials Science, Aalto University, FI-00076 Espoo, Finland*

[b] *Inorganic Materials Chemistry, Ruhr University Bochum, 44801 Bochum, Germany*
¥: equal contribution

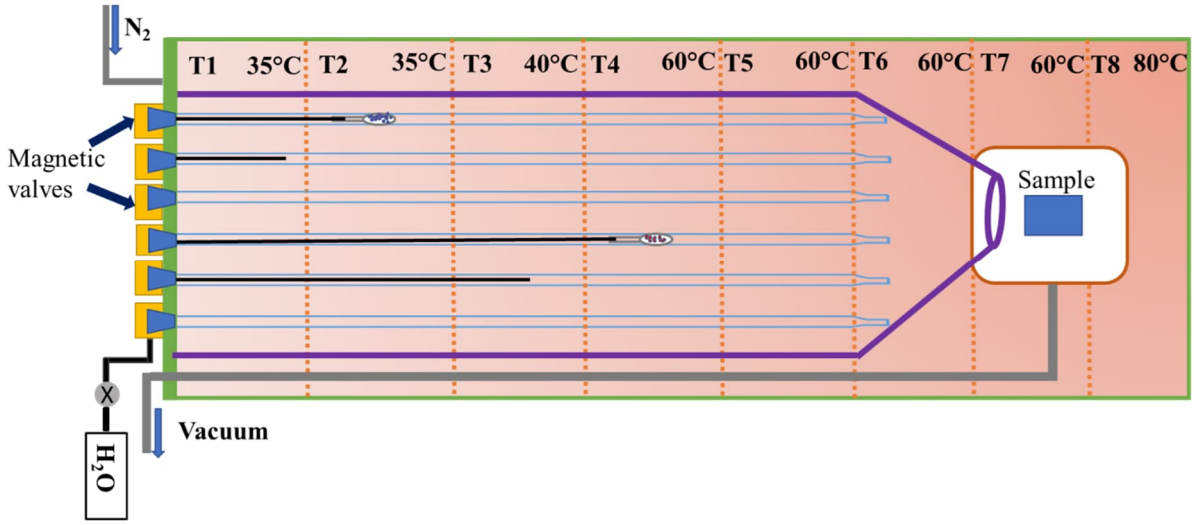

Fig. S1 Schematic diagram of the F-120 ALD reactor used. The temperature profile is demonstrated taking the deposition of Zn-HQ film as an example. Precursors [$Zn(DMP)_2$] and HQ are placed in the T2 and T4 temperature zones, respectively.

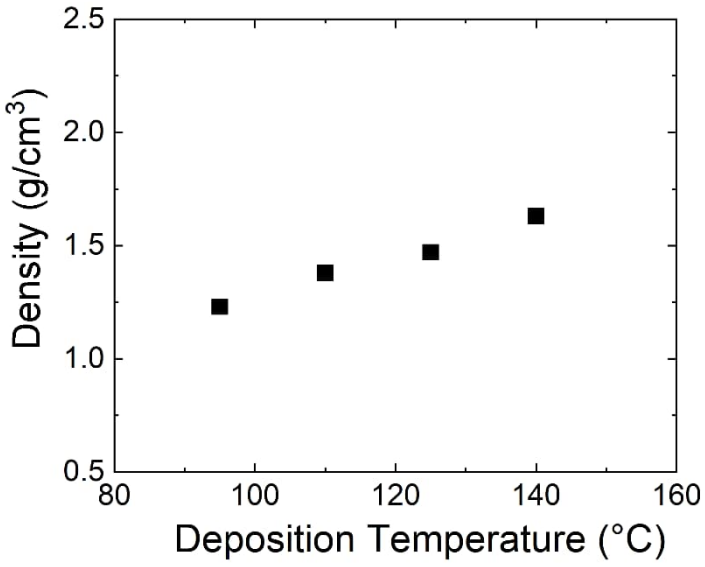

Fig.S2 Densities of Al-HQ films deposited at different temperatures.

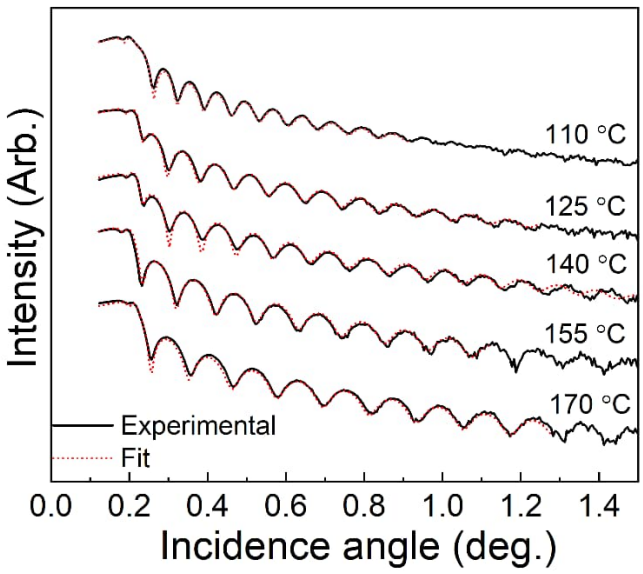

Fig. S3 Comparison of fitted and experimental XRR patterns for Al-HQ films deposited at different temperatures.

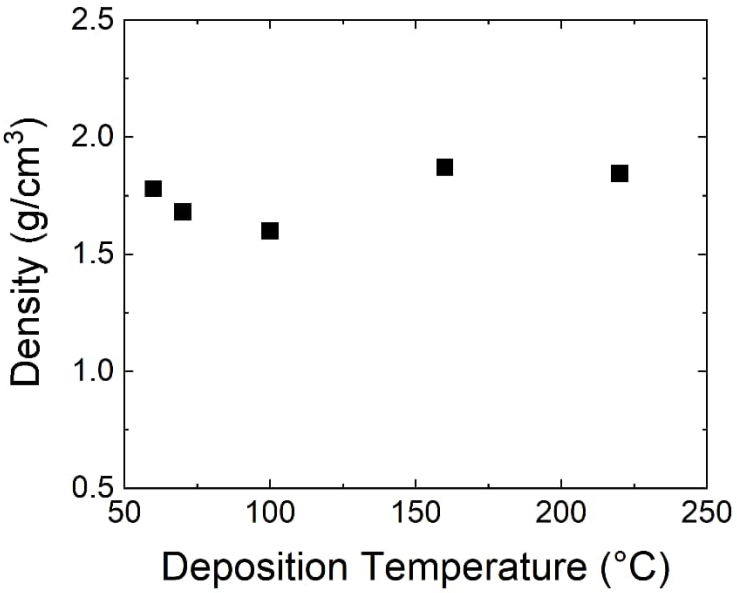

Fig. S4 Densities of Zn-HQ films deposited at different temperatures.

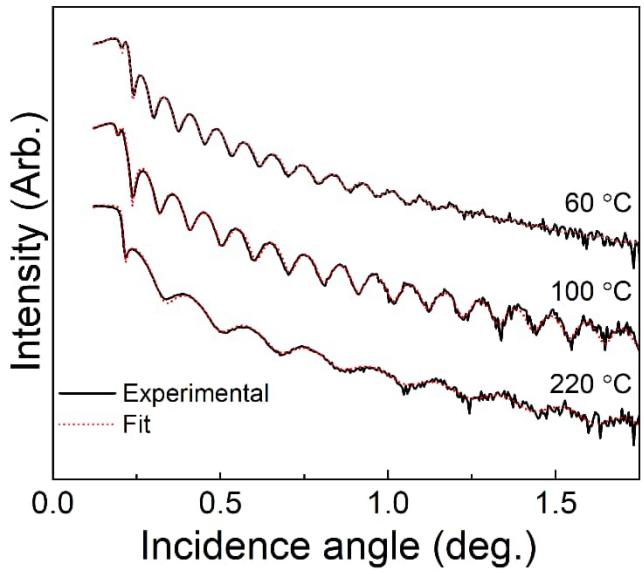

Fig. S5 Comparison of fitted and experimental XRR patterns for Zn-HQ films deposited at different temperatures.